

MOSFET – N-Channel, SUPERFET® II, FRFET®

650 V, 15 A, 260 mΩ

Product Preview FCPF260N65FL1-F154

Description

SUPERFET II MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET II MOSFET is very suitable for the various power system for miniaturization and higher efficiency. SUPERFET II FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

Features

- 700 V @ $T_J = 150^\circ\text{C}$
- $R_{DS(on)} = 220\text{ m}\Omega$ (Typ.)
- Ultra Low Gate Charge (Typ. $Q_g = 46\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 223\text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter

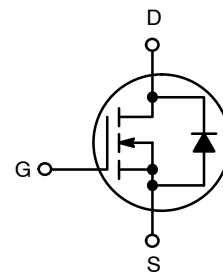
This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.



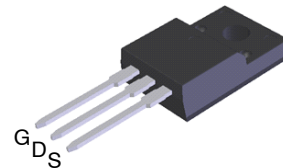
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V_{DSS}	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	260 mΩ @ 10 V	15 A

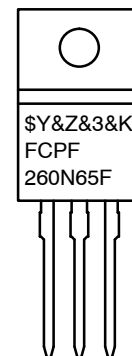


MOSFET



TO-220F Ultra Narrow Lead
CASE 221BN

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot
FCPF260N65F = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain to Source Voltage	650	V
V _{GSS}	Gate to Source Voltage	- DC	±20
		- AC (f > 1 Hz)	±30
I _D	Drain Current	- Continuous (T _C = 25°C)	15
		- Continuous (T _C = 100°C)	9.5
I _{DM}	Drain Current	- Pulsed (Note 1)	45
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	293	mJ
I _{AS}	Avalanche Current (Note 2)	3	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	0.36	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	50	
P _D	Power Dissipation	(T _C = 25°C)	36
		- Derate Above 25°C	0.29
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. I_{AS} = 3 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 7.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 380 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	3.5	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FCPF260N65FL1-F154	FCPF260N65F	TO-220F (Pb-Free)	50 Units / Tube

FCPF260N65FL1-F154

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 10 mA, T _J = 25°C	650	–	–	V
		V _{GS} = 0 V, I _D = 10 mA, T _J = 150°C	700	–	–	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C	–	0.72	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V	–	–	10	μA
		V _{DS} = 520 V, V _{GS} = 0 V, T _C = 125°C	–	40	–	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 1.5 mA	3	–	5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 7.5 A	–	220	260	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 7.5 A	–	14.2	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	–	1760	2340	pF
C _{oss}	Output Capacitance		–	59	80	pF
C _{rss}	Reverse Transfer Capacitance		–	1.0	–	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	–	34	–	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	–	223	–	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 380 V, I _D = 7.5 A, V _{GS} = 10 V (Note 4)	–	46	60	nC
Q _{gs}	Gate to Source Gate Charge		–	9.6	–	nC
Q _{gd}	Gate to Drain "Miller" Charge		–	20	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	0.52	–	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 380 V, I _D = 7.5 A, V _{GS} = 10 V, R _g = 4.7 Ω (Note 4)	–	21.7	54	ns
t _r	Turn-On Rise Time		–	10.5	32	ns
t _{d(off)}	Turn-Off Delay Time		–	54	118	ns
t _f	Turn-Off Fall Time		–	5.8	22	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

I _S	Maximum Continuous Source to Drain Diode Forward Current	–	–	15	A	
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current	–	–	45	A	
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 7.5 A	–	–	1.2	V
t _{rr}	Reverse Recovery Time	V _{DD} = 400 V, I _{SD} = 7.5 A, dI _F /dt = 100 A/μs	–	98	–	ns
Q _{rr}	Reverse Recovery Charge		–	450	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature.

TYPICAL PERFORMANCE CHARACTERISTICS

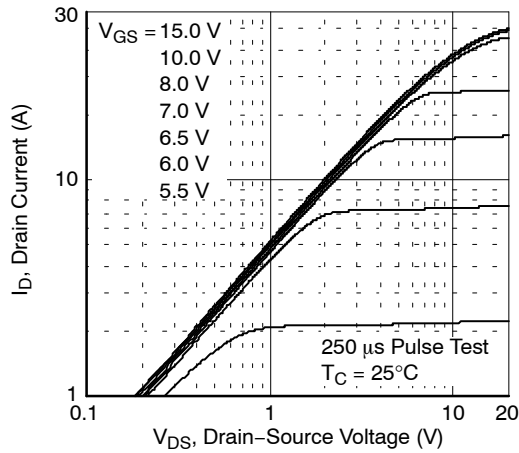


Figure 1. On-Region Characteristics

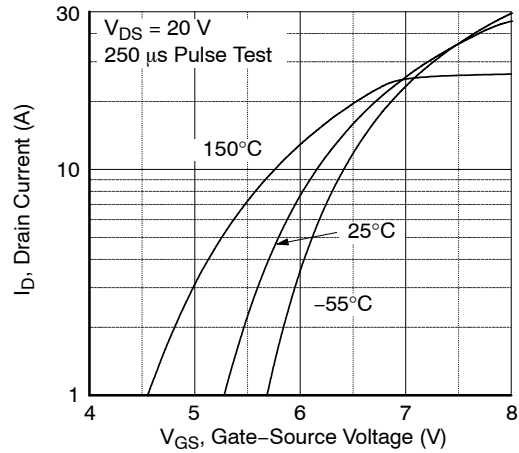


Figure 2. Transfer Characteristics

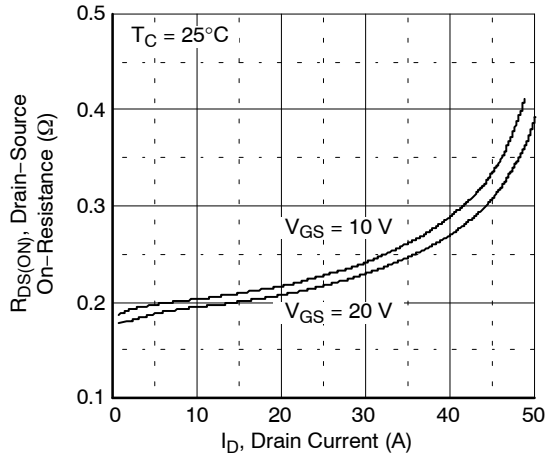


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

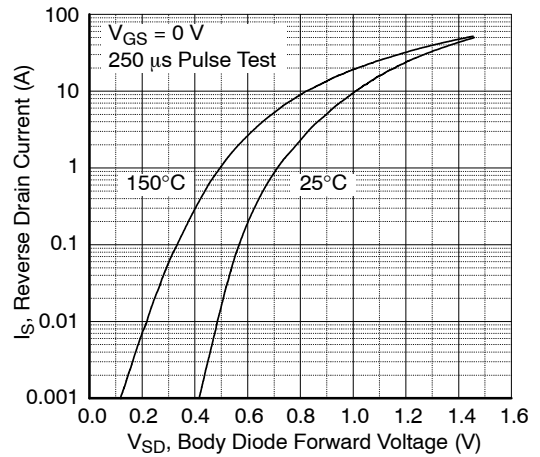


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

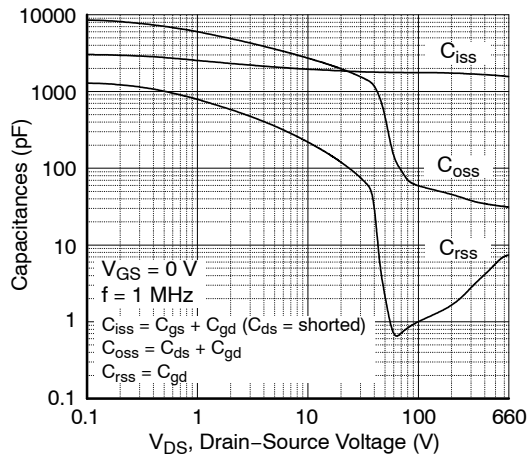


Figure 5. Capacitance Characteristics

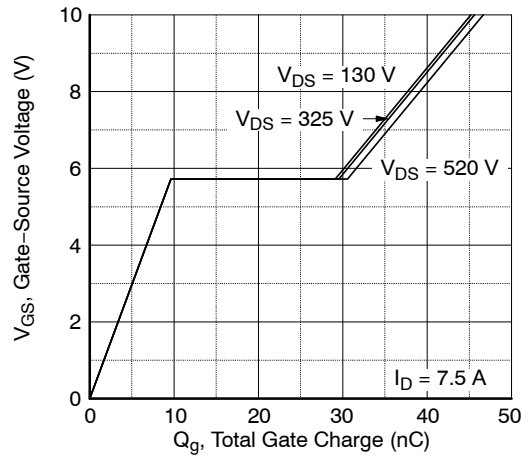


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

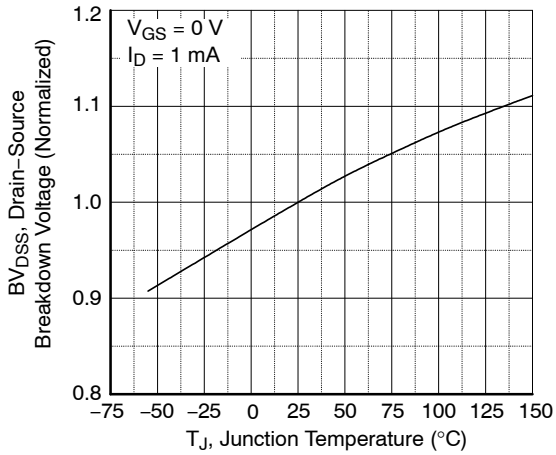


Figure 7. Breakdown Voltage Variation vs. Temperature

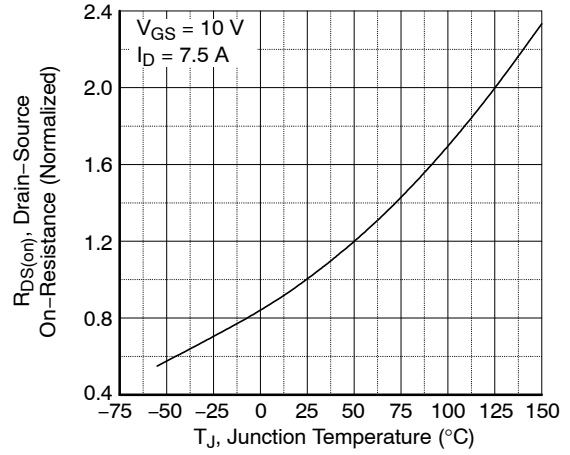


Figure 8. On-Resistance Variation vs. Temperature

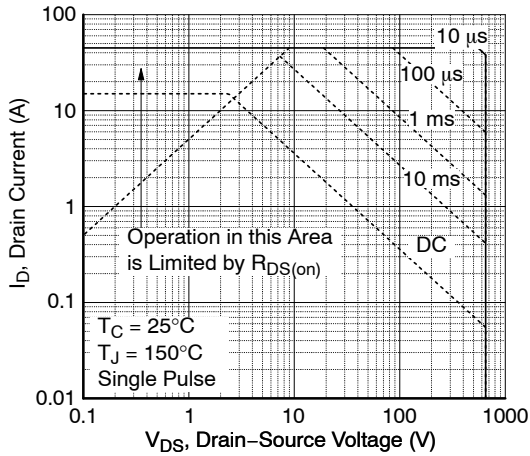


Figure 9. Maximum Safe Operating Area

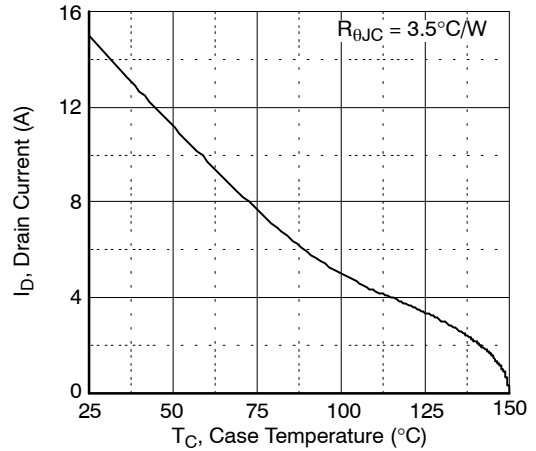


Figure 10. Maximum Drain Current vs. Case Temperature

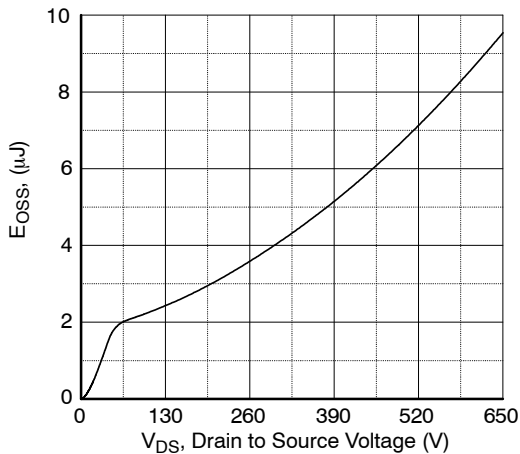


Figure 11. E_{OSS} vs. Drain to Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

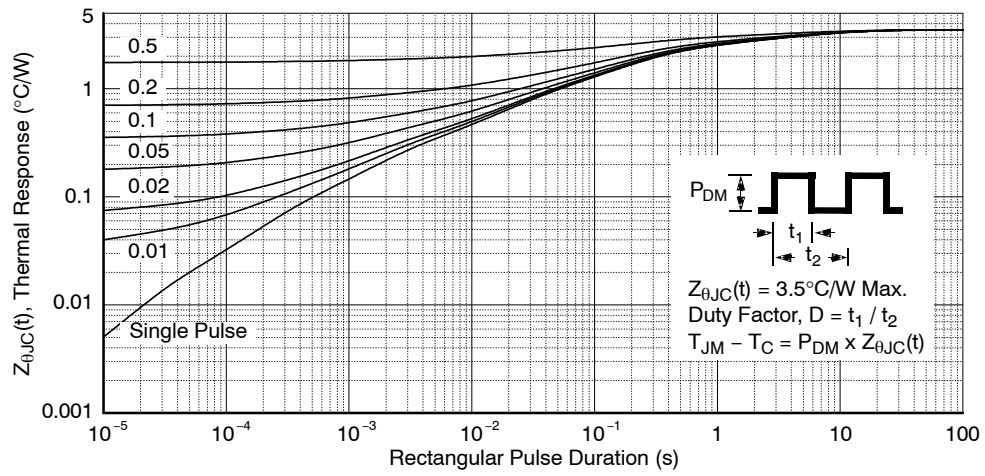


Figure 12. Transient Thermal Response Curve

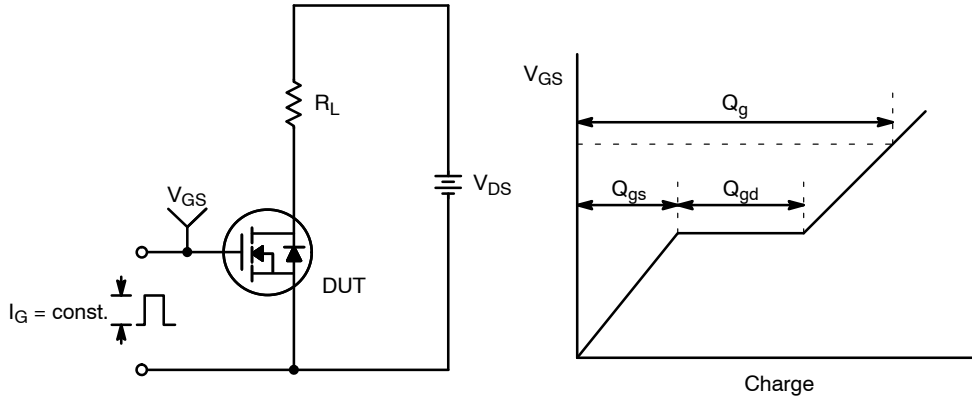


Figure 13. Gate Charge Test Circuit & Waveform

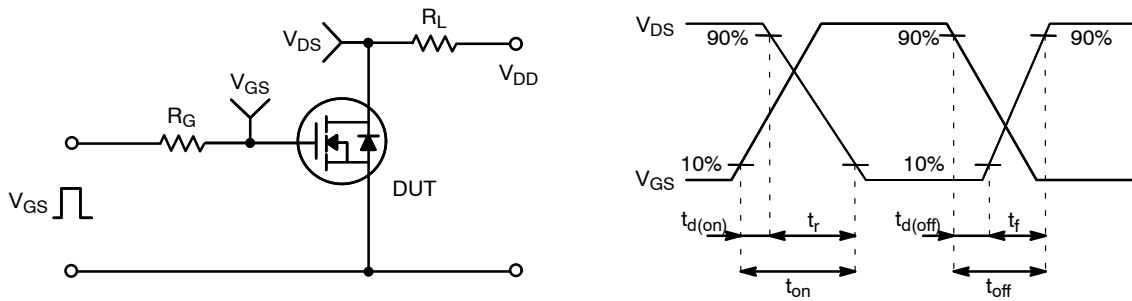


Figure 14. Resistive Switching Test Circuit & Waveforms

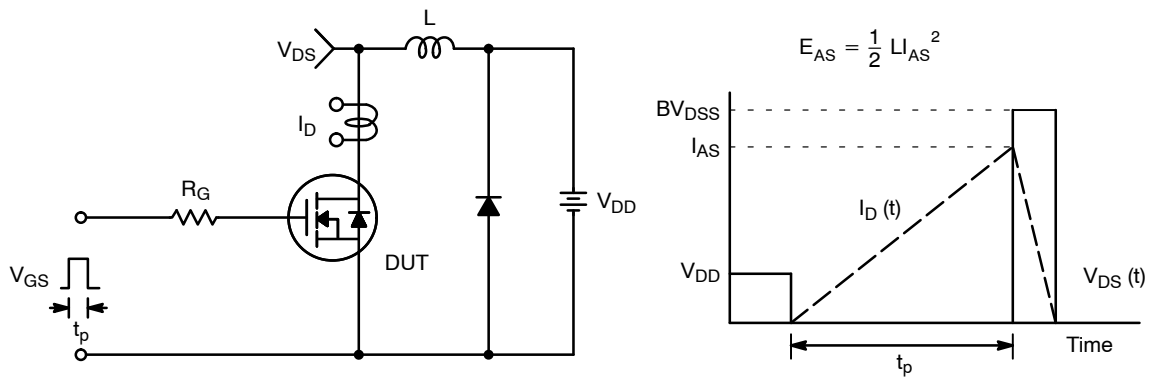


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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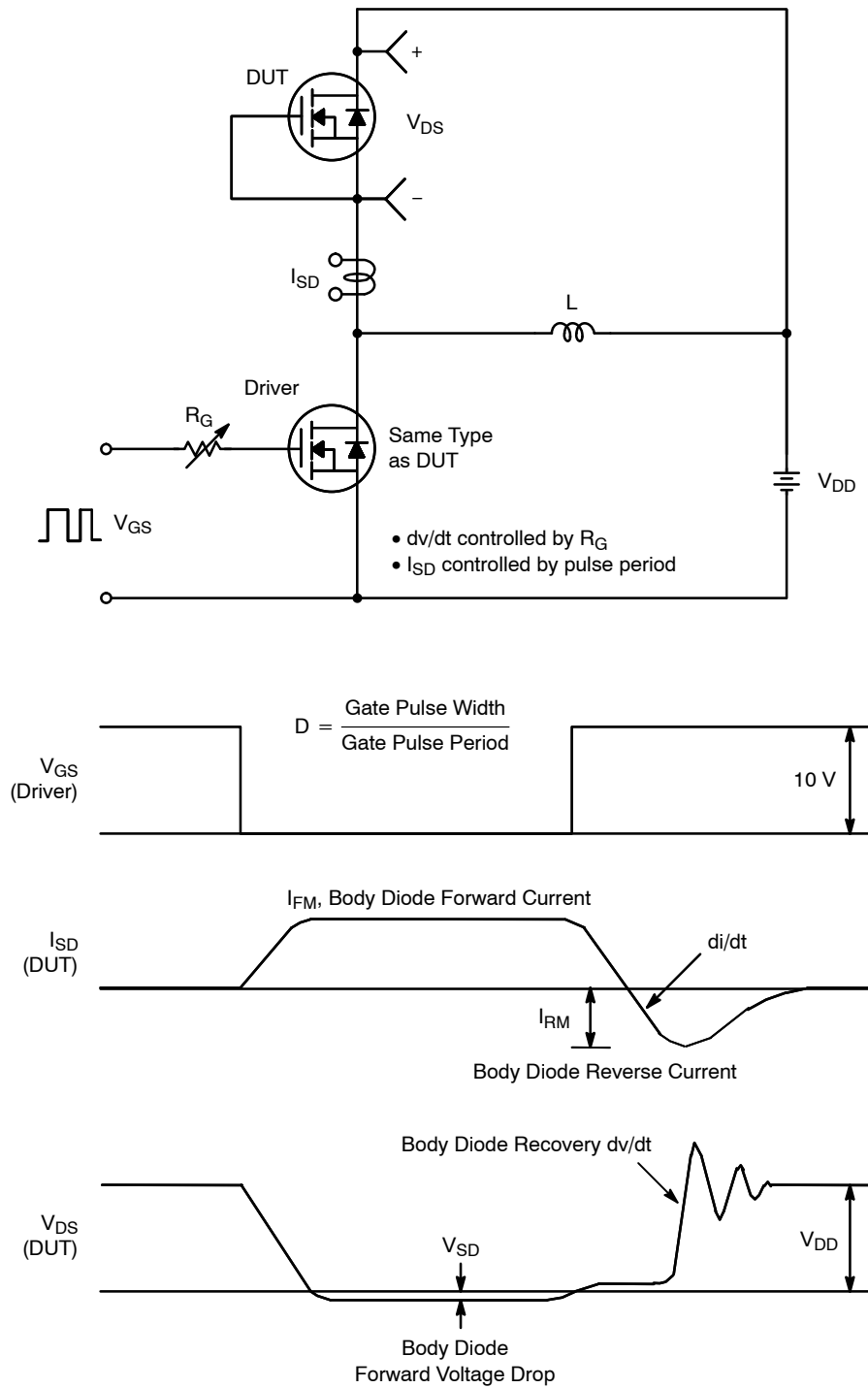


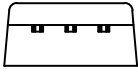
Figure 16. Peak Recovery dv/dt Test Circuit & Waveforms

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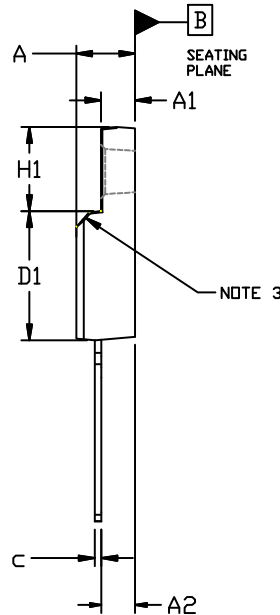
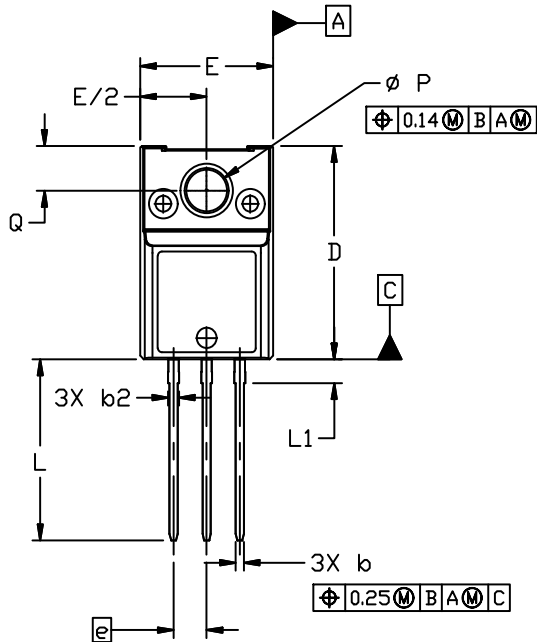
PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD CASE 221BN ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. CONTOUR UNCONTROLLED IN THIS AREA.
4. DIMENSIONS EXCLUDE BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
A1	2.50	2.60	2.70
A2	2.47	2.57	2.67
b	0.56	0.63	0.69
b2	---	---	0.90
c	0.46	0.53	0.59
D	15.80	16.00	16.20
D1	9.58	9.68	9.78
E	10.00	10.20	10.40
e	2.54 BSC		
H1	6.32 REF		
L	13.45	13.60	13.75
L1	1.70	1.80	1.90
P	3.00	3.10	3.20
Q	3.25	3.35	3.45

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